# MOS INTEGRATED CIRCUIT $\mu$ PD16833A

# MONOLITHIC QUAD H BRIDGE DRIVER CIRCUIT

# DESCRIPTION

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The  $\mu$ PD16833A is a monolithic quad H bridge driver IC which uses power MOS FETs in its driver stage. By using the MOS FETs in the output stage, this driver IC has a substantially improved saturation voltage and power consumption as compared with conventional driver circuits using bipolar transistors.

A low-voltage malfunction prevention function is provided to prevent the IC from malfunctioning when the supply voltage drops. By eliminating the charge pump circuit, the current during power-OFF is drastically decreased.

As the package, a 30-pin plastic shrink SOP is employed to enable the creation of compact, slim application sets.

This driver IC can drive two stepping motors at the same time, and is ideal for driving stepping motors in the lens of a video camera.

# FEATURES

- Four H bridge circuits employing power MOS FETs
- Low current consumption by eliminating charge pump
  V<sub>M</sub> pin current when power-OFF: 10 μA MAX. V<sub>DD</sub> pin current: 10 μA MAX.
- Input logic frequency: 100 kHz
- 3-V power supply Minimum operating supply voltage: 2.5 V
- Low-voltage malfunctioning prevention circuit
- 30-pin plastic shrink SOP (300 mil) (μPD16833AG3)

## **ORDERING INFORMATION**

Part Number	Package
μPD16833AG3	30-pin plastic shrink SOP (300 mil)

# ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Parameter	Symbol	Conditions	Rating	Unit
Supply voltage	Vdd		-0.5 to +6.0	V
	Vм		-0.5 to +6.0	V
Input voltage	Vin		-0.5 to V <sub>DD</sub> + 0.5	V
H bridge drive current <sup>Note 1</sup>	DR (DC)	DC	±300	mA
Instantaneous H bridge drive currentNote 1	DR (pulse)	$PW \le 10 \text{ ms}, \text{ Duty} \le 5 \%$	±700	mA
Power dissipation <sup>Note 2</sup>	Рт		1.19	W
Peak junction temperature	Тсн (мах)		150	°C
Storage temperature range	Tstg		–55 to +150	°C

Notes 1. Permissible current per phase, when mounted on a printed circuit board

2. When mounted on a glass epoxy board (10 cm  $\times$  10 cm  $\times$  1 mm)

The information in this document is subject to change without notice.

# **Recommended Operating Conditions**

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply voltage	Vdd	2.5		5.5	V
	Vм	2.7		5.5	V
H bridge drive current	ldr	-200		200	mA
Logic input frequency <sup>Note</sup>	fın			100	kHz
Operating temperature range	TA	-10		85	°C
Peak junction temperature	Тсн (мах)			125	°C

Note Common to IN and EN pins

# DC Characteristics (Unless otherwise specified, $V_{DD} = V_M = 3.0 \text{ V}$ , $T_A = 25 \text{ }^{\circ}\text{C}$ )

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
OFF V <sub>M</sub> pin current	IM (OFF)	with all control pins at low level			10	μΑ
VDD pin current	ldd	with all control pins at low level			10	μΑ
High-level input current	Ін	Vin =Vdd			0.06	mA
Low-level input current	lı.	V <sub>IN</sub> = 0	-1.0			μΑ
Input pull-down resistor	Rind		50		200	kΩ
High-level input voltage	Vін	V <sub>DD</sub> = 2.5 V to 5.5 V	$V_{DD}  imes 0.7$		Vdd + 0.3	V
Low-level input voltage	VIL	V <sub>DD</sub> = 2.5 V to 5.5 V	-0.3		$V_{DD}  imes 0.3$	V
H bridge ON resistance <sup>Note</sup>	Ron	V <sub>DD</sub> = V <sub>M</sub> = 2.7 V to 5.5 V			3.0	Ω
Low-voltage malfunction prevention circuit operating voltage	VDDS1	$V_M = 5.0 V$ -10 °C ≤ T <sub>A</sub> ≤ +85 °C	0.8		2.5	V
	Vdds2	V <sub>M</sub> = 3.0 V −10 °C ≤ T <sub>A</sub> ≤+85 °C	0.65		2.5	V

Note Sum of top and bottom ON resistances (@IDR = 100 mA)

# AC Characteristics (Unless otherwise specified, $V_{DD} = V_M = 3.0 \text{ V}, \text{ T}_A = 25 \text{ }^{\circ}\text{C}$ )

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
H bridge output circuit turn-ON	tonн	$R_M = 20 \Omega$ , Figure 1		0.7	20	μΑ
time						
H bridge output circuit turn-OFF	toffh			0.2	0.5	μΑ
time						
Rise time	tr		0.1	0.4	1.0	μs
Fall time	tr			70	200	ns

# FUNCTION TABLE

Channel 1

EN1	IN <sub>1</sub>	OUT1A	OUT1B
н	L	Н	L
н	Н	L	Н
L	L	Z	Z
L	Н	Z	Z

Channel 3

EN₃	INз	OUT3A	OUT3B
н	L	Н	L
н	Н	L	Н
L	L	Z	Z
L	Н	Z	Z

Channel 2

EN <sub>2</sub>	IN2	OUT2A	OUT2B
н	L	Н	L
н	Н	L	Н
L	L	Z	Z
L	Н	Z	Z

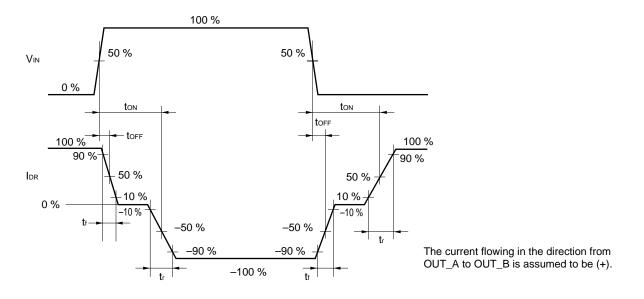
### Channel 4

EN4	IN4	OUT4A	OUT4B
Н	L	Н	L
Н	Н	L	Н
L	L	Z	Z
L	Н	Z	Z

H: High level, L: Low level, Z: High impedance IN

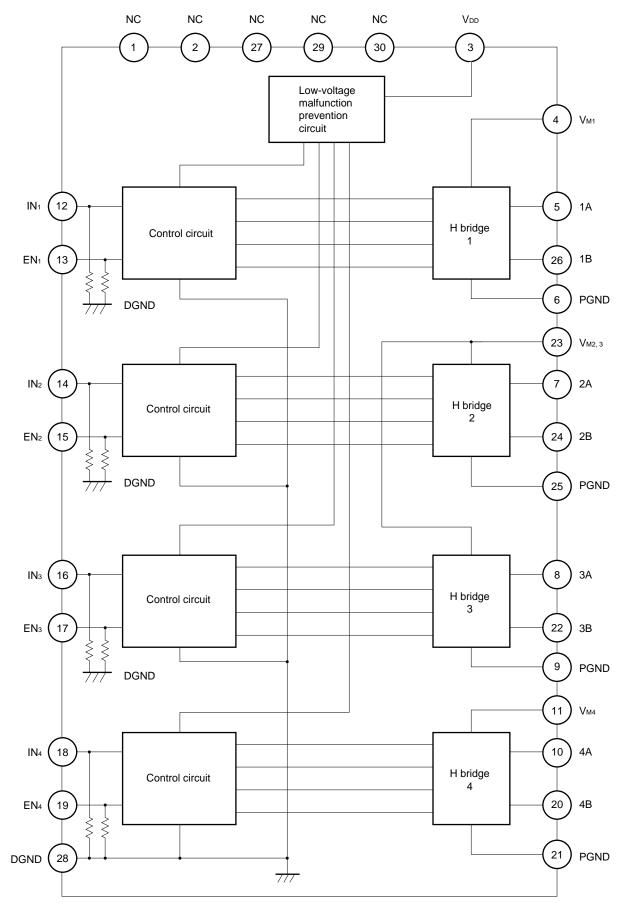
# **PIN CONFIGURATION**

NC	1	30	NC
NC	2	29	NC
Vdd	3	28	DGND
V <sub>M1</sub>	4	27	NC
1A	5	26	1B
PGND	6	25	PGND
2A	7	24	2B
ЗA	8	23	Vм2, з
PGND	9	22	3B
4A	10	21	PGND
V <sub>M4</sub>	11	20	4B
IN1	12	19	EN4
EN1	13	18	IN <sub>4</sub>
IN <sub>2</sub>	14	17	EN₃
EN <sub>2</sub>	15	16	IN₃



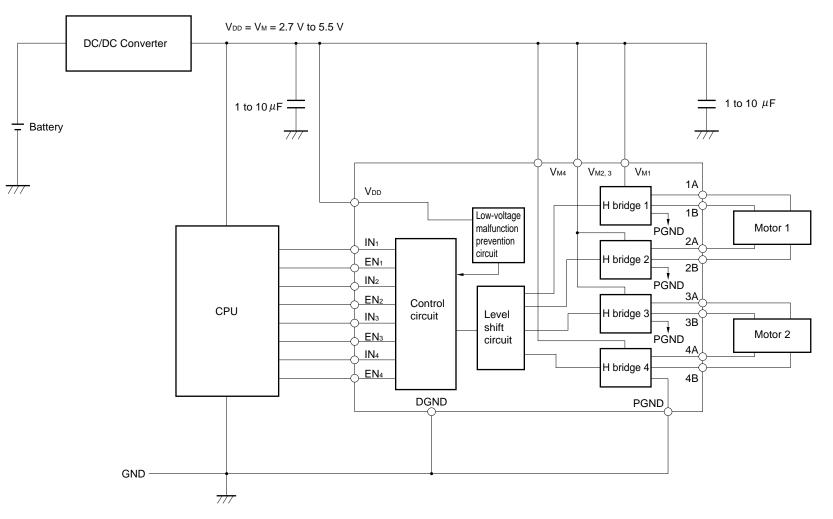
### Figure 1. Switching Characteristic Wave

## **BLOCK DIAGRAM**

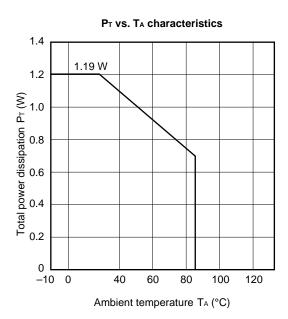




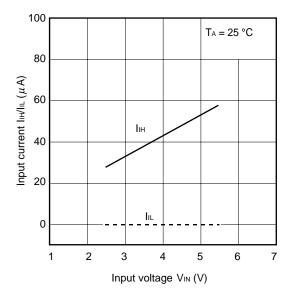


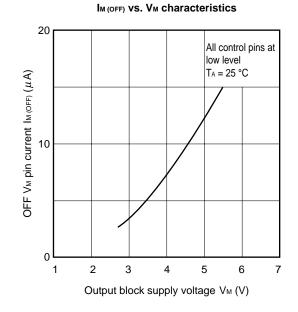


# TYPICAL CHARACTERISTICS (TA = 25 °C)

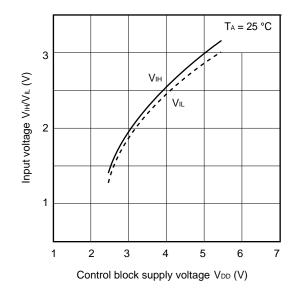






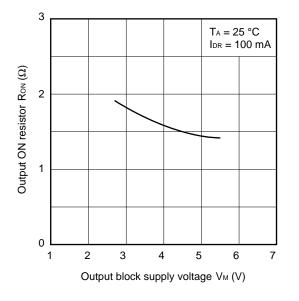


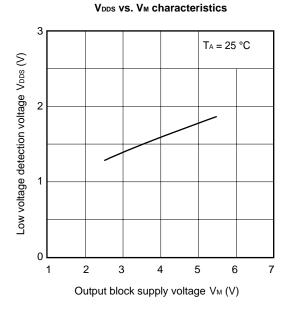
### VIH/VIL vs. VDD characteristics



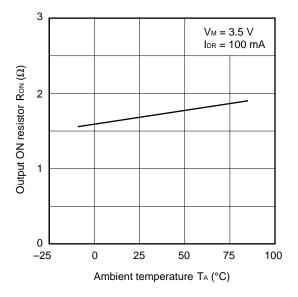
RIND VS. VDD characteristics 200 (CY) 0150 150 100 50 0 1 2 3 4 5 6 7 Control block supply voltage VDD (V)



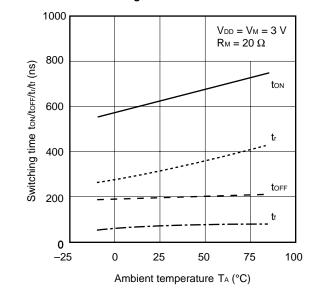




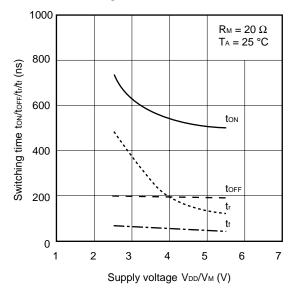




Switching time vs. TA characteristics

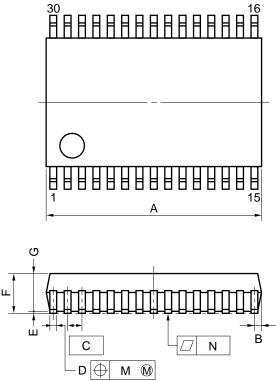


Switching time vs. VDD/VM characteristics



# PACKAGE DIMENSION

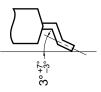
# 30 PIN PLASTIC SHRINK SOP (300 mil)

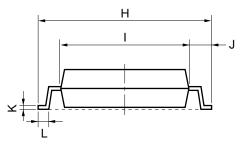




Each lead centerline is located within 0.10 mm (0.004 inch) of its true position (T.P.) at maximum material condition.

detail of lead end





P30GS-65-300B-1

ITEM	MILLIMETERS	INCHES
A	10.11 MAX.	0.398 MAX.
В	0.51 MAX.	0.020 MAX.
С	0.65 (T.P.)	0.026 (T.P.)
D	0.30 <sup>+0.10</sup> 0.05	$0.012\substack{+0.004\\-0.003}$
E	0.125±0.075	0.005±0.003
F	2.0 MAX.	0.079 MAX.
G	1.7±0.1	0.067±0.004
н	8.1±0.2	0.319±0.008
I	6.1±0.2	0.240±0.008
J	1.0±0.2	0.039 <sup>+0.009</sup> -0.008
к	$0.15_{-0.05}^{+0.10}$	$0.006\substack{+0.004\\-0.002}$
L	0.5±0.2	$0.020\substack{+0.008\\-0.009}$
М	0.10	0.004
Ν	0.10	0.004

# **RECOMMENDED SOLDERING CONDITIONS**

It is recommended to solder this product under the conditions described below.

For soldering methods and conditions other than those listed below, consult NEC.

For the details of the recommended soldering conditions of this type, refer to the **Semiconductor Device Mounting Technology Manual (C10535E)**.

Soldering Method	Soldering Conditions	Symbol of Recommended Soldering
Infrared reflow	Peak package temperature: 235 °C, Time: 30 seconds MAX. (210 °C MIN.), Number of times: 3 MAX., Number of days: None <sup>Note</sup> , Flux: Rosin-based flux with little chlorine content (chlorine: 0.2 Wt% MAX.) is recommended.	IR35-00-3
VPS	Peak package temperature: 215 °C, Time: 40 seconds MAX. (200 °C MIN.), (200 °C MIN.), Number of times: 2 MAX., Number of days: None <sup>Note</sup> , Flux: Rosin-based flux with little chlorine content (chlorine: 0.2 Wt% MAX.) is recommended.	VP15-00-2
Wave soldering	Soldering bath temperature: 260 °C MAX., Time: 10 seconds MAX., Preheating temperature: 120 °C MAX., Number of times: 1, Flux: Rosin-based flux with little chlorine content (chlorine: 0.2 Wt% MAX.) is recommended.	WS60-00-1

Note The number of storage days at 25 °C, 65% RH after the dry pack has been opened

### Caution Do not use two or more soldering methods in combination.

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- Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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Anti-radioactive design is not implemented in this product.